



75A, 55V, 0.014 Ohm, N-Channel UltraFET Power MOSFETs

These N-Channel power MOSFETs are manufactured using the innovative UltraFET® process. This advanced process technology achieves the lowest possible on-resistance per silicon area, resulting in outstanding performance. This device is capable of withstanding high energy in the avalanche mode and the diode exhibits very low reverse recovery time and stored charge. It was designed for use in applications where power efficiency is important, such as switching regulators, switching converters, motor drivers, relay drivers, low-voltage bus switches, and power management in portable and battery-operated products.

Formerly developmental type TA75337.

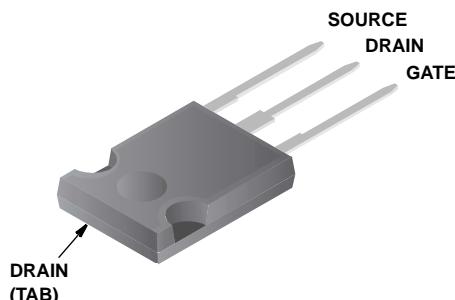
Ordering Information

PART NUMBER	PACKAGE	BRAND
HUF75337G3	TO-247	75337G
HUF75337P3	TO-220AB	75337P
HUF75337S3S	TO-263AB	75337S

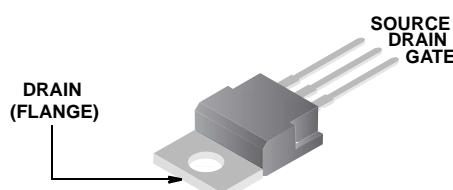
NOTE: When ordering, use the entire part number. Add the suffix T to obtain the TO-263AB variant in tape and reel, e.g., HUF75337S3ST.

Packaging

JEDEC STYLE TO-247



JEDEC TO-220AB



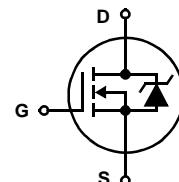
JEDEC TO-263AB



Features

- 75A, 55V
- Simulation Models
 - Temperature Compensated PSPICE® and SABER™ Models
 - SPICE and SABER Thermal Impedance Models Available on the web at: www.fairchildsemi.com
- Peak Current vs Pulse Width Curve
- UIS Rating Curve
- Related Literature
 - TB334, "Guidelines for Soldering Surface Mount Components to PC Boards"

Symbol



HUF75337G3, HUF75337P3, HUF75337S3S

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, Unless Otherwise Specified

			UNITS
Drain to Source Voltage (Note 1)	V_{DSS}	55	V
Drain to Gate Voltage ($R_{GS} = 20\text{k}\Omega$) (Note 1)	V_{DGR}	55	V
Gate to Source Voltage	V_{GS}	± 20	V
Drain Current			
Continuous (Figure 2)	I_D	75	A
Pulsed Drain Current	I_{DM}	Figure 4	
Pulsed Avalanche Rating	E_{AS}	Figure 6	
Power Dissipation	P_D	175	W
Derate Above 25°C		1.17	$^\circ\text{C}/\text{W}$
Operating and Storage Temperature	T_J, T_{STG}	-55 to 175	$^\circ\text{C}$
Maximum Temperature for Soldering			
Leads at 0.063in (1.6mm) from Case for 10s.	T_L	300	$^\circ\text{C}$
Package Body for 10s, See Techbrief 334	T_{pkg}	260	$^\circ\text{C}$

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

1. $T_J = 25^\circ\text{C}$ to 150°C .

Electrical Specifications $T_C = 25^\circ\text{C}$, Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS	
OFF STATE SPECIFICATIONS							
Drain to Source Breakdown Voltage	BV_{DSS}	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$ (Figure 11)	55	-	-	V	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 50\text{V}, V_{GS} = 0\text{V}$	-	-	1	μA	
		$V_{DS} = 45\text{V}, V_{GS} = 0\text{V}, T_C = 150^\circ\text{C}$	-	-	250	μA	
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20\text{V}$	-	-	± 100	nA	
ON STATE SPECIFICATIONS							
Gate to Source Threshold Voltage	$V_{GS(\text{TH})}$	$V_{GS} = V_{DS}, I_D = 250\mu\text{A}$ (Figure 10)	2	-	4	V	
Drain to Source On Resistance	$r_{DS(\text{ON})}$	$I_D = 75\text{A}, V_{GS} = 10\text{V}$ (Figure 9)	-	0.011	0.014	Ω	
THERMAL SPECIFICATIONS							
Thermal Resistance Junction to Case	$R_{\theta JC}$	(Figure 3)	-	-	0.85	$^\circ\text{C}/\text{W}$	
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	TO-247	-	-	30	$^\circ\text{C}/\text{W}$	
		TO-220AB, TO-263AB	-	-	62	$^\circ\text{C}/\text{W}$	
SWITCHING SPECIFICATIONS ($V_{GS} = 10\text{V}$)							
Turn-On Time	t_{ON}	$V_{DD} = 30\text{V}, I_D \leq 75\text{A}, R_L = 0.4\Omega, V_{GS} = 10\text{V}, R_{GS} = 6.2\Omega$	-	-	100	ns	
Turn-On Delay Time	$t_{d(ON)}$		-	13	-	ns	
Rise Time	t_r		-	56	-	ns	
Turn-Off Delay Time	$t_{d(OFF)}$		-	31	-	ns	
Fall Time	t_f		-	28	-	ns	
Turn-Off Time	t_{OFF}		-	-	88	ns	
GATE CHARGE SPECIFICATIONS							
Total Gate Charge	$Q_g(\text{TOT})$	$V_{GS} = 0\text{V}$ to 20V	$V_{DD} = 30\text{V}, I_D \leq 75\text{A}, R_L = 0.4\Omega, I_{g(\text{REF})} = 1.0\text{mA}$ (Figure 13)	-	91	109	nC
Gate Charge at 10V	$Q_g(10)$	$V_{GS} = 0\text{V}$ to 10V		-	51	61	nC
Threshold Gate Charge	$Q_g(\text{TH})$	$V_{GS} = 0\text{V}$ to 2V		-	3.4	4.1	nC
Gate to Source Gate Charge	Q_{gs}			-	9	-	nC
Reverse Transfer Capacitance	Q_{gd}			-	23	-	nC

HUF75337G3, HUF75337P3, HUF75337S3S

Electrical Specifications $T_C = 25^\circ\text{C}$, Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
CAPACITANCE SPECIFICATIONS						
Input Capacitance	C_{ISS}	$V_{DS} = 25\text{V}$, $V_{GS} = 0\text{V}$, $f = 1\text{MHz}$	-	1775	-	pF
Output Capacitance	C_{OSS}	(Figure 12)	-	625	-	pF
Reverse Transfer Capacitance	C_{RSS}		-	150	-	pF

Source to Drain Diode Specifications

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Source to Drain Diode Voltage	V_{SD}	$I_{SD} = 75\text{A}$	-	-	1.25	V
Reverse Recovery Time	t_{rr}	$I_{SD} = 75\text{A}$, $dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	-	85	ns
Reverse Recovered Charge	Q_{RR}	$I_{SD} = 75\text{A}$, $dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	-	180	nC

Typical Performance Curves

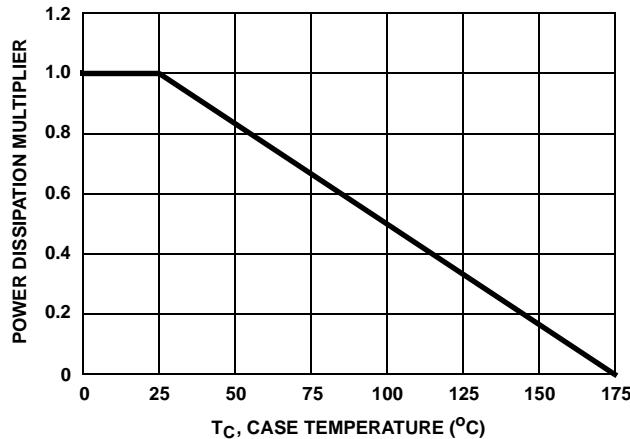


FIGURE 1. NORMALIZED POWER DISSIPATION vs CASE TEMPERATURE

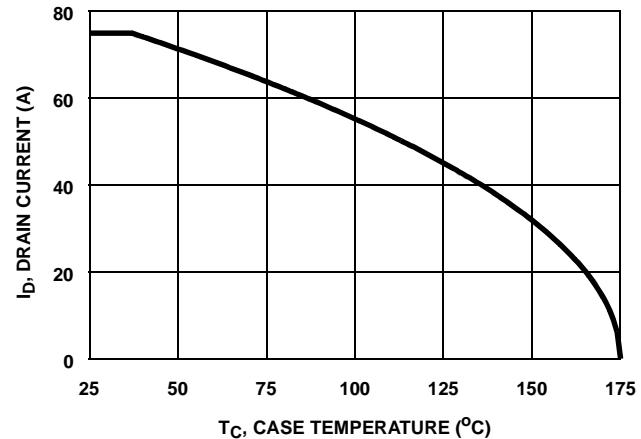


FIGURE 2. MAXIMUM CONTINUOUS DRAIN CURRENT vs CASE TEMPERATURE

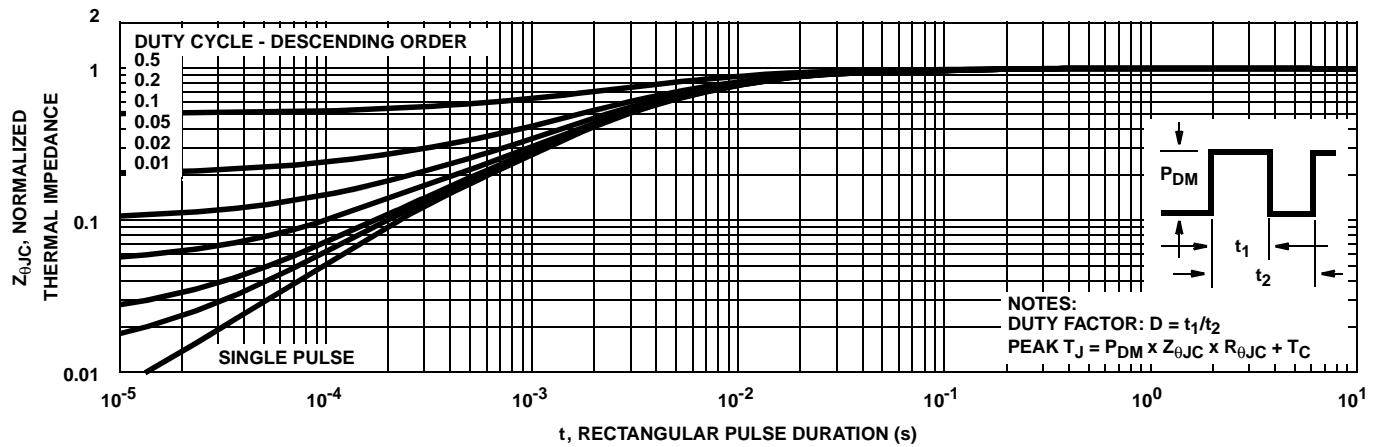


FIGURE 3. NORMALIZED MAXIMUM TRANSIENT THERMAL IMPEDANCE